

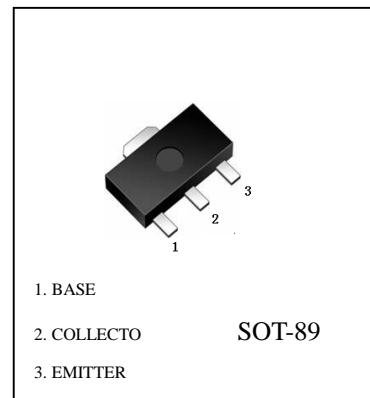
FEATURES

- Low saturation voltage
- Excellent DC current gain characteristics
- Complements to 2SC4672

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current -Continuous	I _C	-2	A
Collector Power dissipation	P _C	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

2SA1797 (PNP)



ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =-50μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{EBO}	I _E =-50μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-500mA	82		270	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1A, I _B =-50mA			-0.35	V
Transition frequency	f _T	V _{CE} =-2V, I _C =-0.5A, f=100MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		36		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q
Range	80-180	120-270
Marking	AGP	AGQ

2SA1797 Typical Characteristics

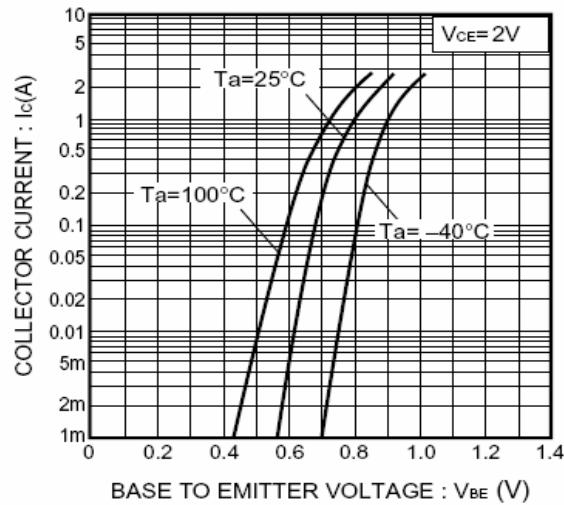


Fig.1 Grounded emitter propagation characteristics

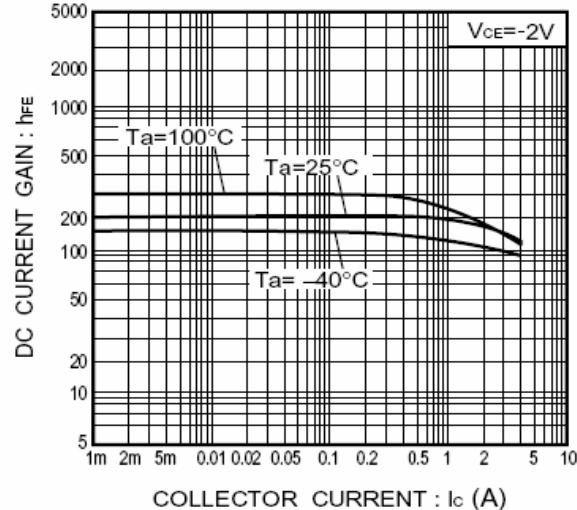


Fig.2 DC current gain vs. collector current

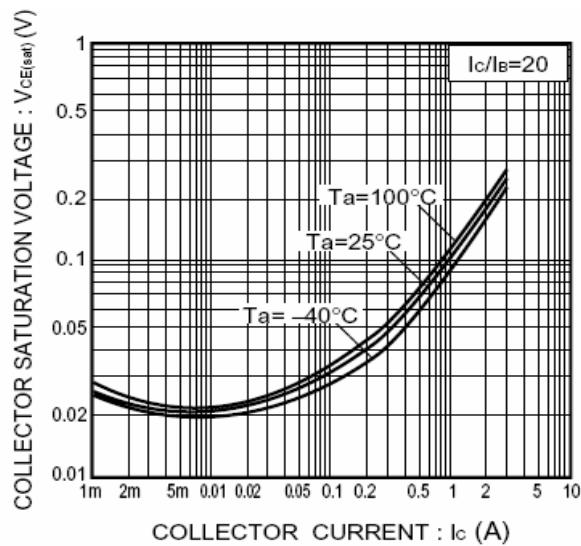


Fig.3 Collector-emitter saturation voltage vs. collector current

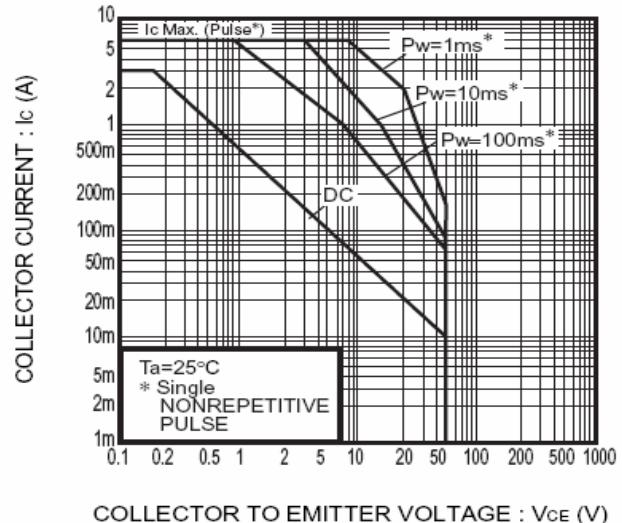


Fig.4 Safe Operating area